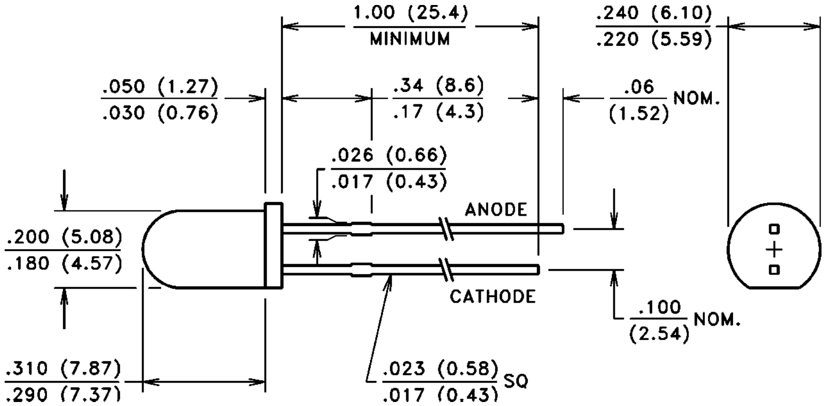
VTP Process Photodiodes

VTP1232H

(Also available in infrared transmitting visible blocking version)

PACKAGE DIMENSIONS inch (mm)



CASE 26 T-1¾

CHIP ACTIVE AREA: .0036 in^2 (2.326 mm^2)

PRODUCT DESCRIPTION

This photodiode features the largest detection area available in a clear, endlooking T-1¾ package. Combined with excellent dark current, it can fulfill the demands of many difficult applications.

ABSOLUTE MAXIMUM RATINGS

Storage Temperature:	-40°C to 100°C
Operating Temperature:	-40°C to 100°C

RoHS Compliant

ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also VTP curves, pages 45-46)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	VTP1232H			UNITS
			Min.	Typ.	Max.	
I_{SC}	Short Circuit Current	H = 100 fc, 2850 K	100			µA
TC I_{SC}	I_{SC} Temperature Coefficient	2850 K		0.20		%/°C
Re	Responsivity	880 nm	0.06	0.076		A/(W/cm^2)
V_{OC}	Open Circuit Voltage	H = 100 fc, 2850 K	.42			mV
TC V_{OC}	V_{OC} Temperature Coefficient	2850 K		-2.0		mV/°C
I_D	Dark Current	H = 0, VR = 10 V			25	nA
C_J	Junction Capacitance	H = 0, V = 0 V		.18	.30	nF
λ_{range}	Spectral Application Range		400		1100	nm
λ_p	Spectral Response - Peak			920		nm
S_R	Sensitivity	@ Peak		0.60		A/W